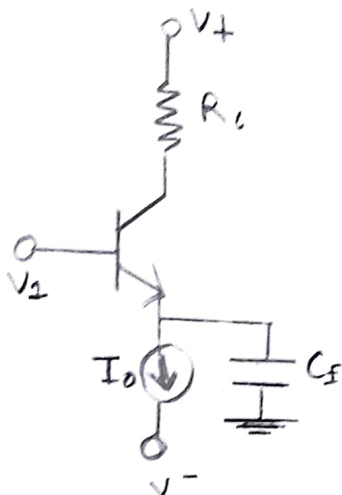


Q.14. Two transistor current source.

other name  $\rightarrow$  current mirror.

A current mirror is nothing but a current source created by a transistor circuit in order to maintain uniformity in current supply.

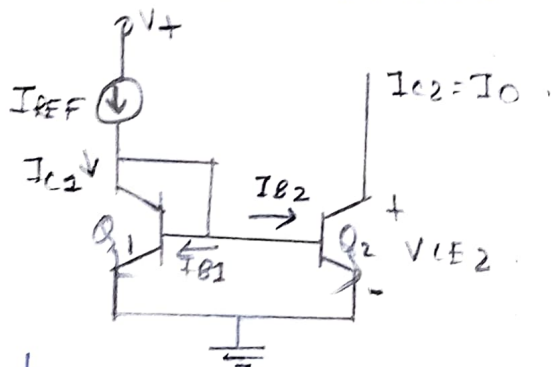
now, considering a BJT :-



when a BJT is connected with a reference current  $I_{REF}$  in short with the Base terminal, we can connect it to another transistor to get a copy of the current source  $I_{REF}$  current "Mirror".

which is why it is called

current mirror :-



↓  
condition

$I_{C1} \approx I_{C2}$   
for current mirror

current Relationship:-

$$I_{REF} = I_{C1} + I_{B1} + I_{B2} \\ = I_{C1} + 2I_{B2}$$

$$\Rightarrow \text{Since } I_{C1} \approx I_{B2}, I_{B2} = I_{C2}/\beta$$

$$\Rightarrow I_{REF} = I_{C2} + 2 \frac{I_{C2}}{\beta} \\ = I_{C2} \left( 1 + \frac{2}{\beta} \right)$$

$$\Rightarrow \left[ I_{C2} = \frac{I_{REF}}{1 + \frac{2}{\beta}} = I_O \right] \rightarrow \text{current relationship.}$$

Output resistance:-

Taking ratio of load current to reference current

$$\frac{I_O}{I_{REF}} = \frac{1}{\left(1 + \frac{2}{\beta}\right)} \times \frac{\left(1 + \frac{V_{CE2}}{V_A}\right)}{\left(1 + \frac{V_{CE1}}{V_A}\right)} \quad V_A = \text{Early effect Voltage.}$$

Reason  
for considering  $V_{CE}$ . In the previous current source circuit, we have a infinite resistance. but in practical, transistors do have a finite resistance which is why  $I_C$  becomes a function of collector emitter voltage.

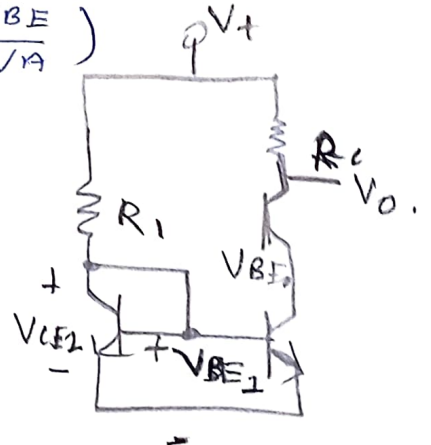
From circuit, we see that  $V_{CE1} = V_{BE}$ .

$\therefore$  differential change:-

$$\frac{dI_O}{dV_{CE2}} = \frac{I_{REF}}{\left(1 + \frac{2}{\beta}\right)} \times \frac{1}{V_A} \times \frac{1}{\left(1 + \frac{V_{BE}}{V_A}\right)}$$

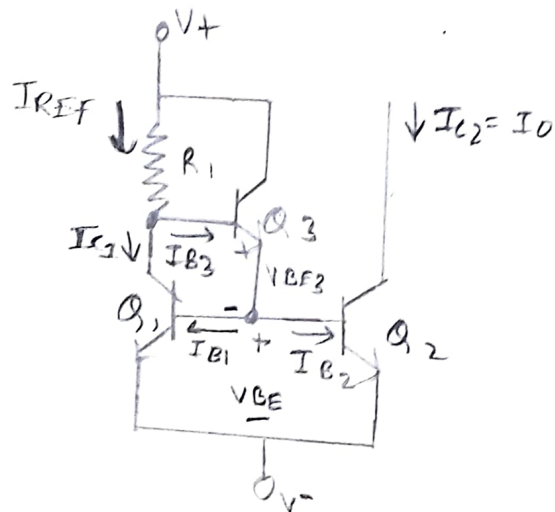
$$\Rightarrow \frac{dI_O}{dV_{CE2}} = \frac{I_O}{V_A} = \frac{1}{r_o}$$

where  $r_o$   
= Output  
resistance.



Q.15. Basic three transistor current source.

Circuit diagram:-



Assuming all transistors are identical

now, since B-E voltage is same for Q1 & Q2,

$$\Rightarrow I_{B1} = I_{B2},$$

$$I_{C1} = I_{C2}$$

currents are supplied to

Q1 & Q2 transistors by Q3

now

Sum of currents at collector node of Q1:-

we get:-

$$I_{REF} = I_{C1} + I_{B3} \quad \text{--- (1)}$$

$$\Rightarrow I_{B1} = I_{B2} = 2I_{B2} = I_{E3} \quad \text{--- (2)}$$

$$\Rightarrow I_{E3} = (1 + \beta_3) I_{B3} \quad \text{--- (3)}$$

Solving (1), (2), (3), we get:-

$$I_{E3} = (1 + \beta_3) I_{B3}$$

$$I_{REF} = I_{C1} + \frac{I_{E3}}{(1 + \beta_3)} = I_{C1} + \frac{2I_{B2}}{(1 + \beta_3)}$$

$\Rightarrow I_{C1} \Rightarrow I_{C2}$  &  $I_{B2} = I_{C2}/\beta$ ; we get:-

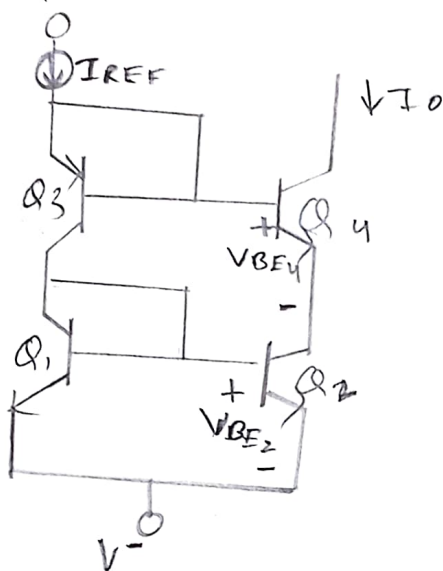
$$I_{REF} = I_{C2} + \frac{2I_{C2}}{\beta(1 + \beta_3)} = I_{C2} \left[ 1 + \frac{2}{\beta(1 + \beta_3)} \right]$$

∴ The output current  $I_O := (I_{C2})$

$$\Rightarrow I_O = I_{C2} = \frac{I_{REF}}{\left[ 1 + \frac{2}{\beta(1+\beta_3)} \right]}$$

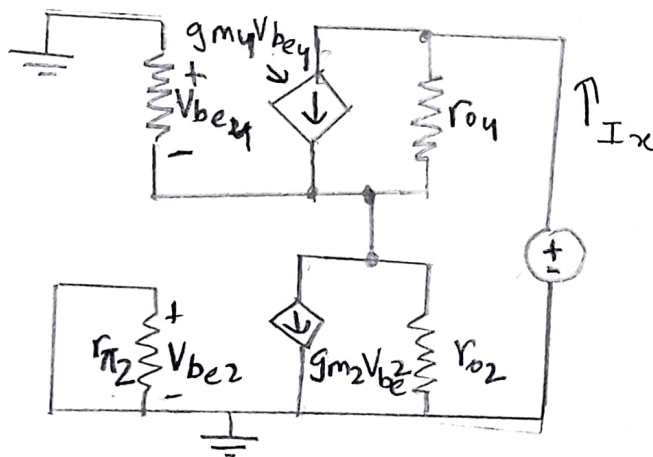
8.16.

### Cas code Current Mirror



If the transistors are matched, i.e. if their device parameters are identical, then the load and reference currents are equal.

Small signal equivalent of above circuit.



In above circuit since  $g_{m2} V_{BE2} = 0$ ,  
 $V_{BE4} = -I_x(r_{o2} || r_{\pi4})$ .

$$\Rightarrow I_x = g_{m4} V_{be4} + \left( \frac{V_x - I_x (r_{o2} \parallel r_{\pi4})}{r_{o4}} \right)$$

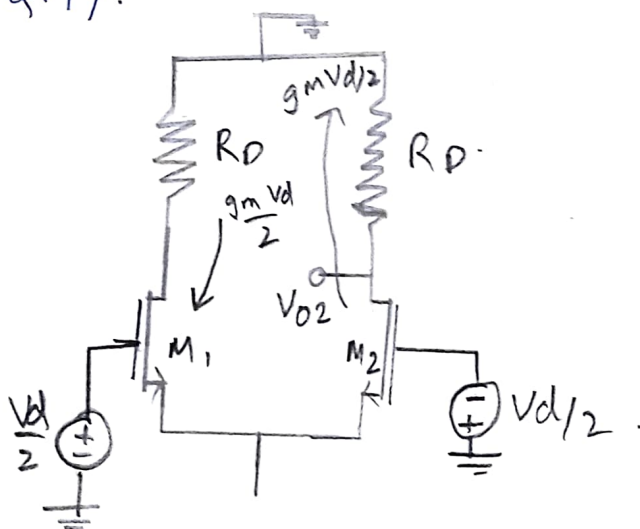
$$= -g_{m4} I_x (r_{o2} \parallel r_{\pi4}) + \left( \frac{V_x - I_x (r_{o2} \parallel r_{\pi4})}{r_{o4}} \right)$$

assuming  $r_{\pi4} \ll r_{o2}$ ,

$$\left[ R_o = \frac{V_x}{I_x} = r_{o4} (1 + \beta) + r_{\pi4} \approx \beta r_{o4} \right]$$

⇒ The output resistance has increased by a factor of  $\beta$  compared to the two transistors current source which increases the stability of current source with changes in output voltage.

Q.17.



→ differential voltage gain.

$$A_d = \frac{V_o}{V_d} = \frac{g_m R_D}{2}$$

$$= \sqrt{\frac{k_n I_Q}{2}} \times R_D$$

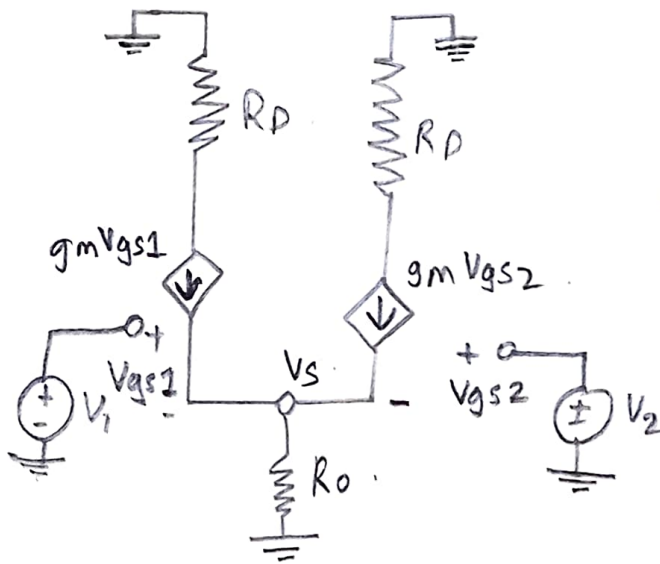
↓  
Small signal equivalent:-

All voltages are represented by their phasor components:-

Two transistors are biased at the same current

$$\Rightarrow g_{m1} = g_{m2} = g_m$$





KCL at  $V_S$ :-

$$gmV_{gs1} + gmV_{gs2} = \frac{V_S}{R_D}$$

$$\therefore V_{gs1} = V_1 - V_S, \quad V_{gs2} = V_2 - V_S$$

$$gm(V_1 + V_2 - 2V_S) = \frac{V_S}{R_D}$$

Solving for  $V_S$ :-

$$V_S = \frac{V_1 + V_2}{2 + \frac{1}{gmR_D}}, \quad V_O = V_{d2} = -(gmV_{gs2})R_D = -(gmR_D)(V_2 - V_S)$$

using above two equations we get:-

$$V_O = -gmR_D \left[ \frac{V_2 \left( 1 + \frac{1}{gmR_D} \right) - V_1}{2 + \frac{1}{gmR_D}} \right] \quad \text{--- (1)}$$

now Equation (1) can be written as.

$$V_O = \frac{gmR_D V_d}{2} - \frac{gmR_D}{1 + 2gmR_D} V_{cm} \quad \text{--- (2)}$$

Output voltage general form:-

$$V_O = A_d V_d + A_{cm} V_{cm} \quad \text{--- (3)}$$

→ transconductance:-

$$gm = 2\sqrt{knI_{DQ}} = \sqrt{2knI_{DQ}}$$

⇒ comparing (2) & (3).

$$A_d = \frac{gmR_D}{2} = \sqrt{2knI_{DQ}} \left( \frac{R_D}{2} \right) = \sqrt{\frac{knI_{DQ}}{2}} R_D$$

8 common mode gain:-

$$A_{cm} = \frac{-g_m R_D}{1 + 2g_m R_D} = \frac{-\sqrt{2k_n I_Q} \cdot R_D}{1 + 2\sqrt{2k_n I_Q} \cdot R_D}$$

now, we know

$$\text{CMRR (common mode rejection ratio)} \\ = |A_d/A_{cm}|$$

$\therefore$  from above equations:-

$$\text{CMRR} = \frac{1}{2} [1 + 2\sqrt{2k_n I_Q} \cdot R_D]$$

Q18.

$$R_D = \frac{1}{2I_Q} = \frac{1}{(0.02)(0.5)} = 100 \text{ k}\Omega$$

$$A_d = \sqrt{\frac{k_n I_Q}{2}} = 8, \quad A_{cm} = \sqrt{2(1)(0.5)(16)}$$

where

$k_n = 1$  here.

$$\text{CMRR} = 20 \log_{10} \left( \frac{8}{0.0798} \right) \\ = 40.045$$